

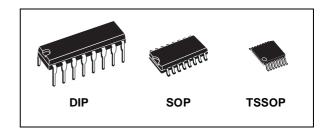
# M74HC4052

# DUAL 4-CHANNEL ANALOG MULTIPLEXER

- LOW POWER DISSIPATION:  $I_{CC} = 4\mu A(MAX.)$  at  $T_A=25^{\circ}C$
- LOGIC LEVEL TRANSLATION TO ENABLE 5V LOGIC SIGNAL TO COMMUNICATE WITH ±5V ANALOG SIGNAL
- LOW "ON" RESISTANCE:  $70\Omega$  TYP. ( $V_{CC}$  -  $V_{EE}$  = 4.5V)  $50\Omega$  TYP. ( $V_{CC}$  -  $V_{EE}$  = 9V)
- WIDE ANALOG INPUT VOLTAGE RANGE: ±6V
- FAST SWITCHING: t<sub>od</sub> = 15ns (TYP.) at T<sub>A</sub> = 25 °C
- LOW CROSSTALK BETWEEN SWITCHES
- HIGH ON/OFF OUTPUT VOLTAGE RATIO
- WIDE OPERATING SUPPLY VOLTAGE RANGE (V<sub>CC</sub> V<sub>EE</sub>) = 2V TO 12V
- LOW SINE WAVE DISTORTION: 0.02% at V<sub>CC</sub> - V<sub>EE</sub> = 9V
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28 % V<sub>CC</sub> (MIN.)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 4052

#### **DESCRIPTION**

The M74HC4052 is a dual four-channel analog MULTIPLEXER/DEMULTIPLEXER fabricated with silicon gate C<sup>2</sup>MOS technology and it is pin to pin compatible with the equivalent metal gate CMOS4000B series.



#### **ORDER CODES**

PACKAGE	TUBE	T & R				
DIP	M74HC4052B1R					
SOP	M74HC4052M1R	M74HC4052RM13TR				
TSSOP		M74HC4052TTR				

It contains 8 bidirectional and digitally controlled analog switches.

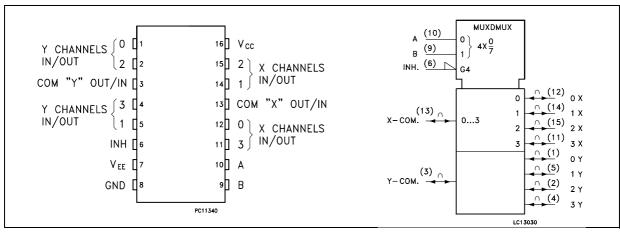
A built-in level shifting is included to allow an input range up to  $\pm 6V$  (peak) for an analog signal with digital control signal of 0 to 6V.

V<sub>EE</sub> supply pin is provided for analog input signals. It has an inhibit (INH) input terminal to disable all the switches when high. For operation as a digital multiplexer/demultiplexer, VEE is connected to GND.

A and B control inputs select one channel out of four in each section.

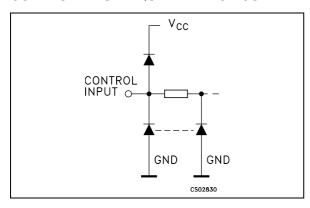
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS

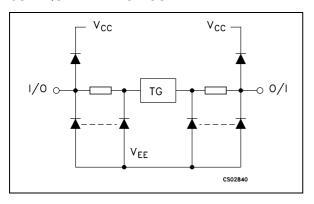


July 2001 1/12

# **CONTROL INPUT EQUIVALENT CIRCUIT**



# I/O EQUIVALENT CIRCUIT



# **PIN DESCRIPTION**

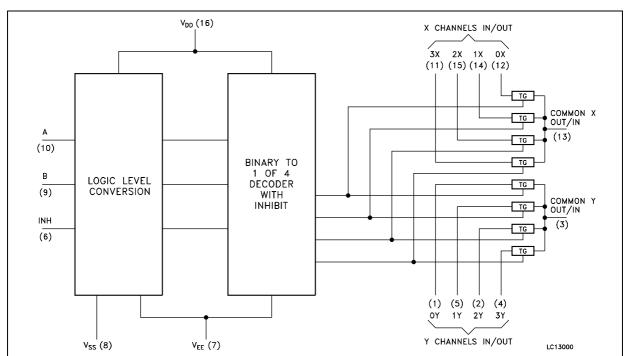
PIN No	SYMBOL	NAME AND FUNCTION
1, 5, 2, 4	0Y to 3Y	Independent Input Outputs
6	INH	INHIBIT Input
7	$V_{EE}$	Negative Supply Voltage
10, 9	A, B	Select Inputs
12, 14, 15, 11	0X to 3X	Independent Input Outputs
3	COM Y OUT/IN	Common X Output/Input
13	COM Y OUT/IN	Common Y Output/Input
8	GND	Ground (0V)
16	V <sub>CC</sub>	Positive Supply Voltage

#### **TRUTH TABLE**

II	NPUT STAT	ON CHANNEL	
INH	В	Α	ON CHANNEL
L	L	L	0X, 0Y
L	L	Н	1X, 1Y
L	Н	L	2X, 2Y
L	Н	Н	3X, 3Y
Н	Х	Х	NONE

X: Don't care

### **FUNCTIONAL DIAGRAM**



# **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>CC</sub> - V <sub>EE</sub>	Supply Voltage	-0.5 to +13	V
V <sub>I</sub>	Control Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>I/O</sub>	Switch I/O Voltage	$V_{EE}$ -0.5 to $V_{CC}$ + 0.5	V
I <sub>CK</sub>	Control Input Diode Current	± 20	mA
I <sub>IOK</sub>	I/O Diode Current	± 20	mA
I <sub>T</sub>	Switch Through Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
$P_{D}$	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	Supply Voltage		2 to 6	V
V <sub>EE</sub>	Supply Voltage		-6 to 0	V
V <sub>CC</sub> - V <sub>EE</sub>	Supply Voltage		2 to 12	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V	
V <sub>I/O</sub>	I/O Voltage		V <sub>EE</sub> to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V <sub>CC</sub> = 2.0V	0 to 1000	
t <sub>r</sub> , t <sub>f</sub>		V <sub>CC</sub> = 4.5V	0 to 500	ns
		V <sub>CC</sub> = 6.0V	0 to 400	

# **DC SPECIFICATIONS**

			Test	Condition				Value	)				
Symbol	Parameter	V <sub>CC</sub>	V <sub>EE</sub>		Т		T <sub>A</sub> = 25°C		85°C	-55 to	125°C	Unit	
		(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
V <sub>IHC</sub>	High Level Input	2.0			1.5			1.5		1.5			
	Voltage	4.5			3.15			3.15		3.15		V	
		6.0			4.2			4.2		4.2			
$V_{ILC}$	Low Level Input	2.0					0.5		0.5		0.5		
	Voltage						1.35		1.35		1.35	V	
		6.0					1.8		1.8		1.8		
R <sub>ON</sub>	ON Resistance	4.5	GND	$V_I = V_{IHC}$ or $V_{ILC}$		85	180		225		270		
		4.5	-4.5	$V_{I/O} = V_{CC}$ to $V_{EE}$		55	120		150		180		
		6.0	-6.0	I <sub>I/O</sub> ≤ 2mA		50	100		125		150		
		2.0	GND	\/ \/ or \/		150						Ω	
		4.5	GND	$V_I = V_{IHC}$ or $V_{ILC}$		70	150		190		230		
		4.5	-4.5	$V_{I/O} = V_{CC} \text{ or } V_{EE}$ $I_{I/O} \le 2\text{mA}$		50	100		125		150		
		6.0	-6.0	11/O = 2111A		45	80		100		120		
$\Delta R_{ON}$	Difference of ON	4.5	GND	$V_I = V_{IHC}$ or $V_{ILC}$		10	30		35		45		
	Resistance	4.5		$V_{I/O} = V_{CC}$ or $V_{EE}$		5	12		15		18	Ω	
	between switches	6.0	-6.0	$I_{I/O} \le 2mA$		5	10		12		15		
I <sub>OFF</sub>	Input/Output	6.0	GND	$V_{OS} = V_{CC}$ or			±0.06		± 0.6		± 1.2		
	Leakage Current (SWITCH OFF)	6.0		$\begin{aligned} & \text{GND} \\ & \text{V}_{\text{IS}} = \text{GND or V}_{\text{CC}} \\ & \text{V}_{\text{I}} = \text{V}_{\text{ILC}} \text{ or V}_{\text{IHC}} \end{aligned}$			± 0.1		± 1		± 2	μΑ	
I <sub>IZ</sub>	Switch Input	6.0	GND	$V_{OS} = V_{CC}$ or			±0.06		± 0.6		± 1.2		
Leakage Current (SWITCH ON, OUTPUT OPEN)		6.0		$\begin{array}{c} \text{GND} \\ \text{V}_{\text{I}} = \text{V}_{\text{IHC}} \text{ or } \text{V}_{\text{ILC}} \end{array}$			± 0.1		± 1		± 2	μΑ	
I <sub>I</sub>	Input Leakage Current	6.0	GND	$V_I = V_{CC}$ or GND			± 0.1		± 0.1		± 1	μΑ	
I <sub>CC</sub>	I <sub>CC</sub> Quiescent Supply	6.0	GND	$V_1 = V_{CC}$ or GND			4		40		80	μΑ	
	Current	6.0	-6.0	AI - ACC OLGIAD			8		80		160		

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ns}$ )

			Test	Condition	Value							
Symbol	Parameter	v <sub>cc</sub>	V <sub>EE</sub>		T,	T <sub>A</sub> = 25°C			85°C	-55 to 125°C		Unit
		(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
$\Phi_{I/O}$	Phase Difference	2.0	GND			25	60		75		90	
	Between Input and	4.5	GND			6	12		15		18	
	Output	6.0	GND			5	10		13		15	ns
		4.5	-4.5			4						
t <sub>PZL</sub>	Output Enable	2.0	GND			64	225		280		340	- ns
t <sub>PZH</sub>	Time	4.5	GND	$R_1 = 1K\Omega$		18	45		56		68	
		6.0	GND	$N_{\perp} = 1N22$		15	38		48		58	
		4.5	-4.5			18						
t <sub>PLZ</sub>	Output Disable	2.0	GND			100	250		315		375	
t <sub>PHZ</sub>	Time	4.5 GND	D 41/0		33	50		63		70	nc	
		6.0	GND	$R_L = 1K\Omega$		28	43		54		64	ns
		4.5	-4.5			29						

# **CAPACITIVE CHARACTERISTICS**

	Parameter		Test Condition		Value							
Symbol		V <sub>CC</sub> (V)	V <sub>EE</sub>		T <sub>A</sub> = 25°C			-40 to	85°C	-55 to 125°C		Unit
			( <del>\(\bar{V}\)</del>	ı	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance	5.0				5	10		10		10	pF
C <sub>I/O</sub>	Common Terminal Capacitance	5.0	-5.0			19	40		40		40	pF
C <sub>I/O</sub>	Switch Terminal Capacitance	5.0	-5.0			7	15		15		15	pF
C <sub>IOS</sub>	Feed Through Capacitance	5.0	-5.0			0.85	2		2		2	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0	GND			71						pF

<sup>1)</sup>  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$ 

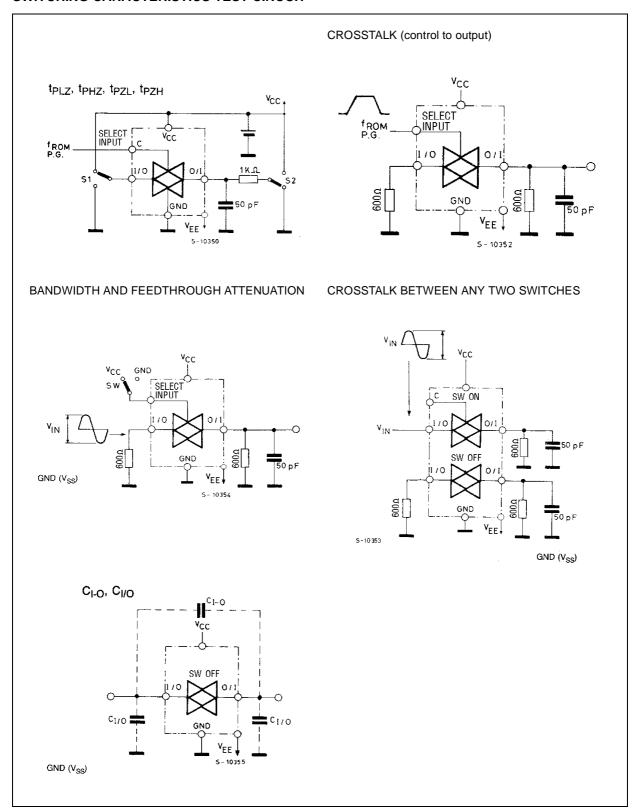
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# ANALOG SWITCH CHARACTERISTICS (GND = 0V; $T_A = 25$ °C)

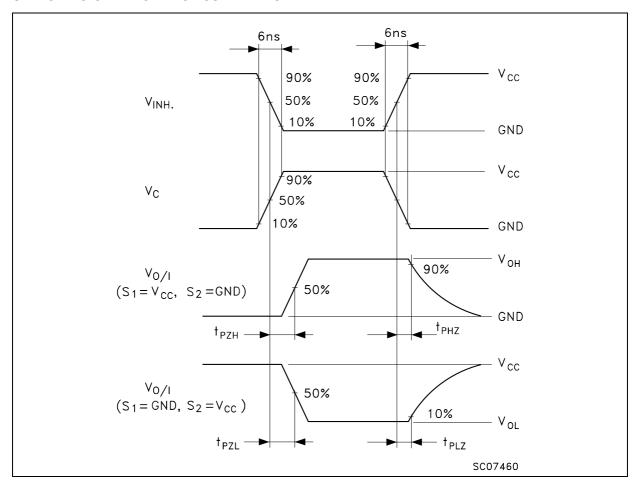
Symbol	Parameter				Test Condition	Value	Unit
		V <sub>CC</sub> (V)	V <sub>EE</sub> (V)	V <sub>IN</sub> (V <sub>p-p</sub> )		Тур.	
	Sine Wave	2.25	-2.25	4		0.025	
	Distortion	4.5	-4.5	8	$f_{IN}$ = 1 KHz $R_L$ = 10 K $\Omega$ , $C_L$ = 50 pF	0.020	%
		6.0	-6.0	11		0.018	
$f_{MAX}$	Frequency	2.25	-2.25		Adjust f <sub>IN</sub> voltage to obtain 0 dBm at V <sub>OS</sub> .	120	
	Response	4.5	-4.5	Ind	crease f <sub>IN</sub> Frequency until dB meter reads -3dB	190	MHz
	(Switch ON) (*)	6.0	-6.0		$R_L$ = 50 $\!\Omega,C_L$ = 10 pF, $f_{IN}$ = 1KHz sine wave	200	
$f_{MAX}$	Frequency	2.25	-2.25		Adjust f <sub>IN</sub> voltage to obtain 0 dBm at V <sub>OS</sub> .	70	
	Response	4.5	-4.5	Ind	crease f <sub>IN</sub> Frequency until dB meter reads -3dB	110	MHz
	(Switch ON) (**)	6.0	-6.0		$R_L$ = 50 $\!\Omega,C_L$ = 10 pF, $f_{IN}$ = 1KHz sine wave	140	
	Feedthrough	2.25	-2.25		V <sub>IN</sub> is centered at (V <sub>CC</sub> - V <sub>EE</sub> )/2	-50	
	Attenuation (Control of the Control	4.5	-4.5		Adjust input for 0 dBm	-50	dB
	(Switch OFF)	6.0	-6.0		$R_L = 600\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ KHz sine wave	-50	
	Crosstalk (Control	2.25	-2.25		Adjust $R_L$ at set up so that $I_S = 0A$ .	60	
	Input to Signal	4.5	-4.5	R	$_{L}$ = 600 $\Omega$ , C $_{L}$ = 50 pF, f $_{IN}$ = 1KHz square wave	140	mV
	Output)	6.0	-6.0			200	
	Crosstalk	2.25	-2.25		Adjust V <sub>IN</sub> to obtain 0dBm at input	-50	
	(between any two	4.5	-4.5		$R_L = 600\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ KHz sine wave	-50	dB
	Switches)	6.0	-6.0	1		-50	

<sup>(\*)</sup> Input COMMON Terminal, and measured at SWITCH Terminal (\*\*) Input SWITCH Terminal, and measured at common Terminal NOTE: These characteristics are determined by the design of the device.

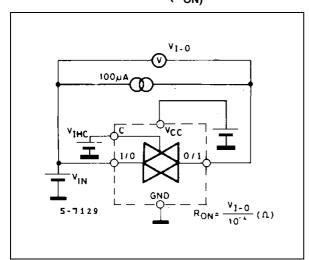
# **SWITCHING CARACTERISTICS TEST CIRCUIT**



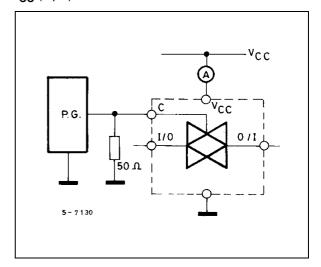
# **SWITCHING CHARACTERISTICS WAVEFORM**



# CHANNEL RESISTANCE (R<sub>ON)</sub>

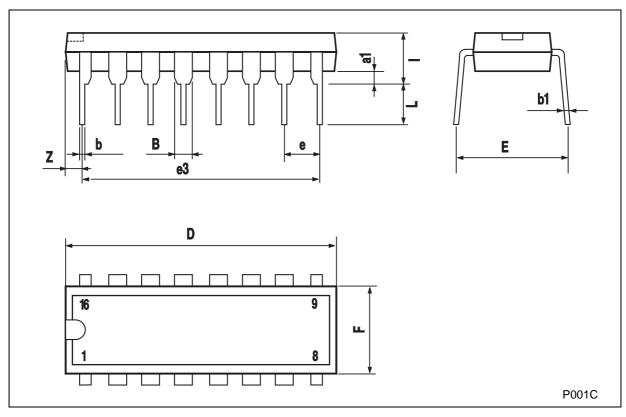


# I<sub>CC</sub> (Opr.)



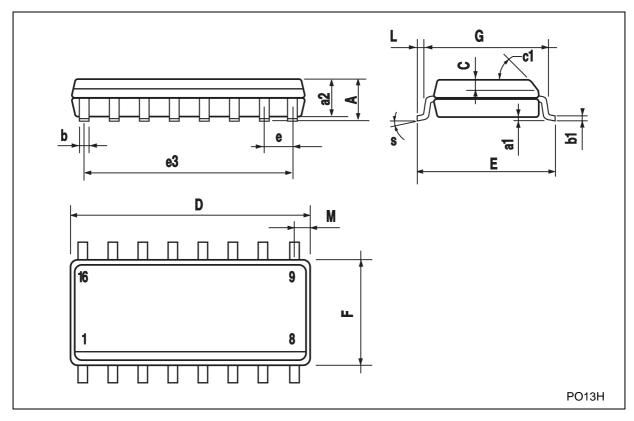
# Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
Е		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



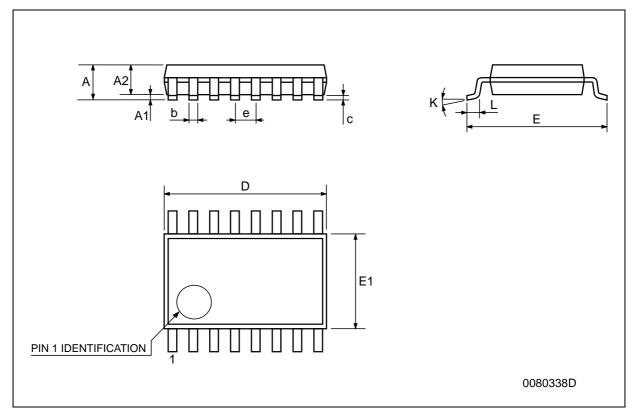
# **SO-16 MECHANICAL DATA**

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)	•	•
D	9.8		10	0.385		0.393
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S		-	8° (	max.)		4



# **TSSOP16 MECHANICAL DATA**

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



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